



**WANSEMI**  
万芯半导体

**WP3400SS**

# **Enhancement Mode N-Channel Power MOSFET**

**SOT23/NMOS/30V/ $\pm 12$ V/0.95V/5.8A/28m $\Omega$**

**Rev1.9**

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## 30V, 28mΩ, 5.8A, Single N-Channel

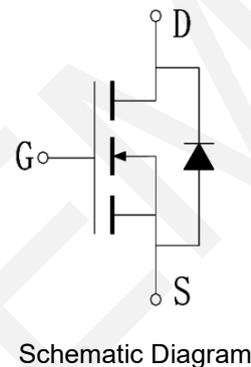
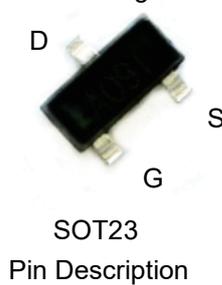
### 1.Features

- ◆ 30V MOSFET technology
- ◆ Low on-state resistance
- ◆ Fast switching
- ◆  $V_{GS} \pm 12V$

$V_{DS}$	$R_{DS(on)}$ Typ.	$I_D$ Max.
30V	28mΩ @ 10V	5.8A
	30mΩ @ 4.5V	
	36mΩ @ 2.5V	

### 2.Applications

- ◆ Power Switching Application
- ◆ Load Switching



### 3. Package Marking and Ordering Information

Part no.	Marking	Package	PCS/Reel	PCS/CTN.
WP3400SS	A09T	SOT23	3,000	180,000

### 4.Absolute Max Ratings at $T_a=25^\circ C$ (Note1)

Parameter	Symbol	Maximum	Units
Drain to Source Voltage	$V_{DSS}$	30	V
Gate to Source Voltage	$V_{GSS}$	$\pm 12$	V
Drain Current (DC)	$I_D$	5.8	A
Drain Current (Pulse), $PW \leq 300\mu s$	$I_{DP}$	30	A
Total Dissipation	$P_D$	1.4	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature	$T_{stg}$	-55 to +150	$^\circ C$

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**5. Thermal Resistance Ratings (Note 2)**

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	89	$^{\circ}C/W$

Note 2: When mounted on 1 inch square copper board  $t \leq 10\text{sec}$  The value in any given application depends on the user's specific board design.

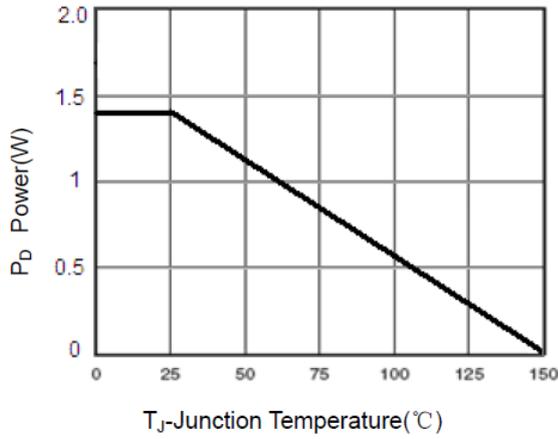
**6. Electrical Characteristics at  $T_a=25^{\circ}C$  (Note 3)**

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Drain to Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	30	-	-	V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 30V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate to Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{DS} = 250\mu A$	0.5	0.95	1.5	V
Static Drain to Source On-State Resistance	$R_{DS(on)}$	$I_D = 5.8A, V_{GS} = 10V$	-	28	32	m $\Omega$
		$I_D = 5A, V_{GS} = 4.5V$	-	30	35	m $\Omega$
		$I_D = 3A, V_{GS} = 2.5V$	-	36	45	m $\Omega$
Input Capacitance	$C_{iss}$	$V_{GS} = 0V,$ $V_{DS} = 15V,$ Frequency = 1.0MHz	-	820	-	pF
Output Capacitance	$C_{oss}$		-	99	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	77	-	pF
Turn-ON Delay Time	$t_{d(on)}$	$V_{DD} = 15V, R_L = 2.7\Omega,$ $V_{GS} = 10V, R_G = 3\Omega$	-	3.3	-	ns
Rise Time	$t_r$		-	4.8	-	ns
Turn-OFF Delay Time	$t_{d(off)}$		-	26	-	ns
Fall Time	$t_f$		-	4	-	ns
Total Gate Charge	$Q_g$	$V_{DS} = 15V,$ $V_{GS} = 4.5V,$ $I_D = 5A$	-	9.5	-	nC
	$Q_{gs}$		-	1.5	-	nC
	$Q_{gd}$		-	3	-	nC
Diode Forward Voltage	$V_{FSD}$	$I_S = 5A, V_{GS} = 0$	-	0.9	1.2	V

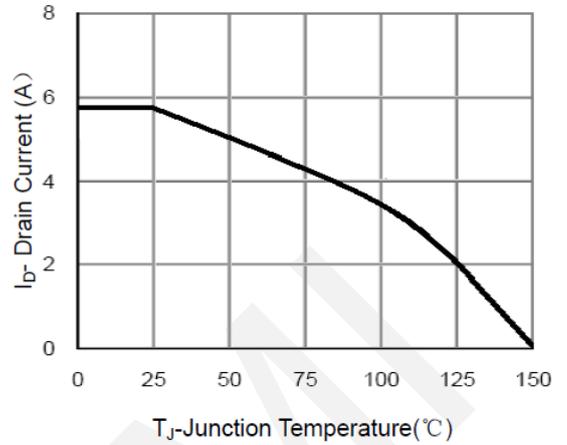
Note 3: Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



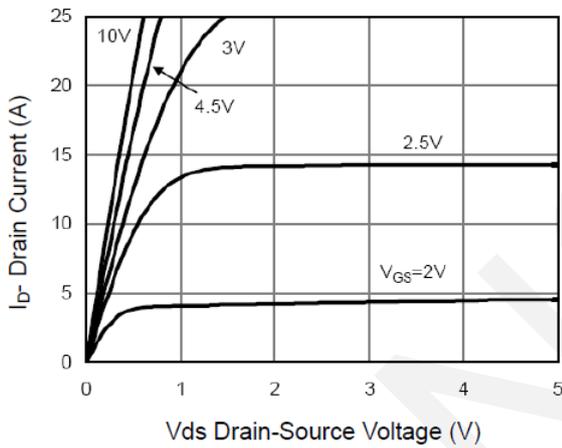
### 7. Typical Electrical and Thermal Characteristics



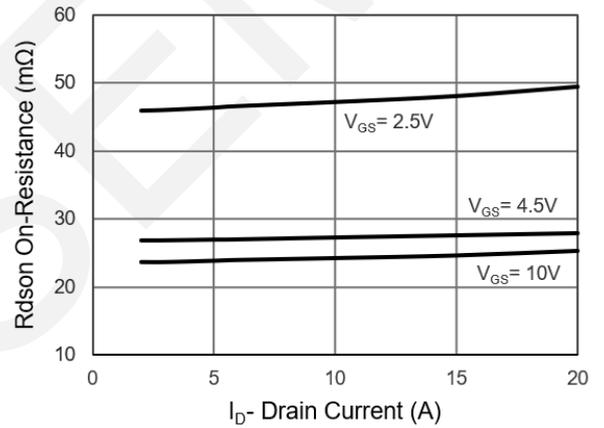
Power Dissipation



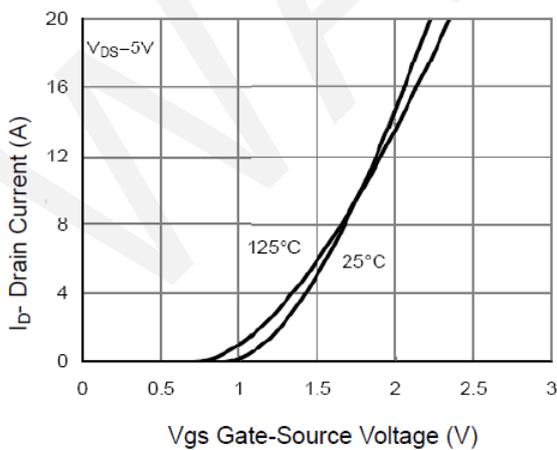
Drain Current



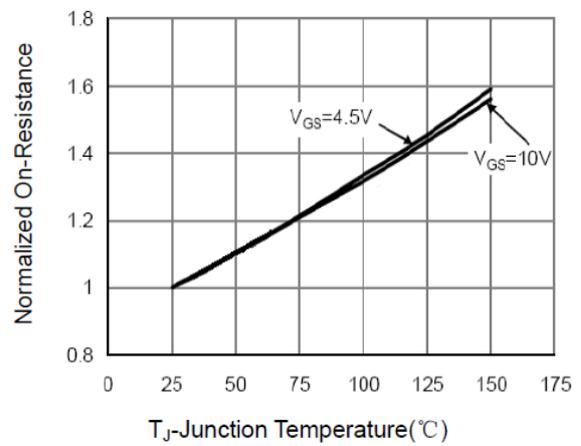
Output Characteristics



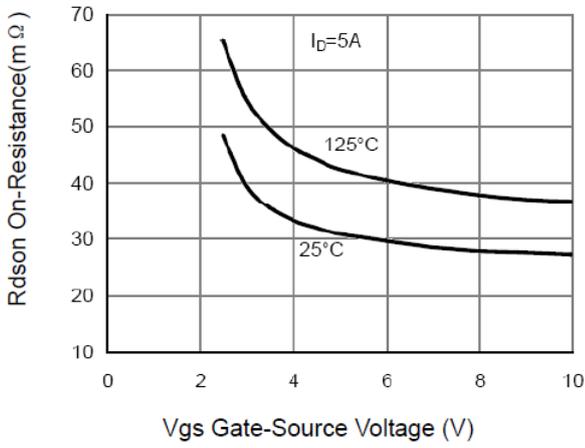
Drain-Source On-Resistance



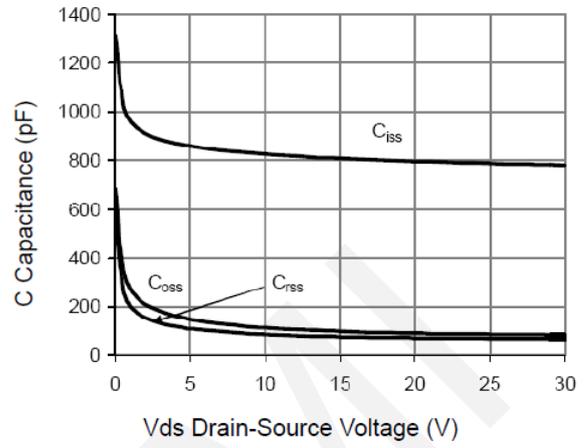
Transfer Characteristics



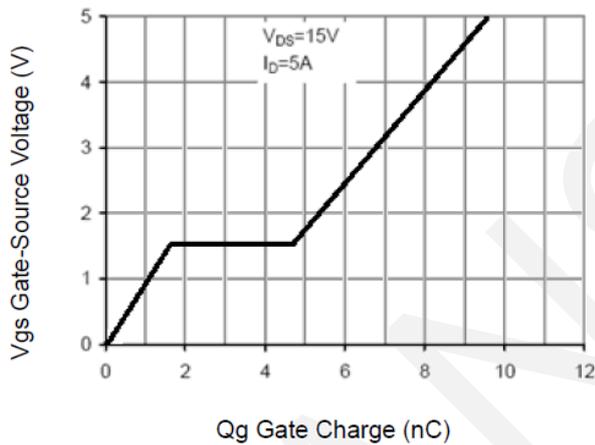
Drain-Source On-Resistance



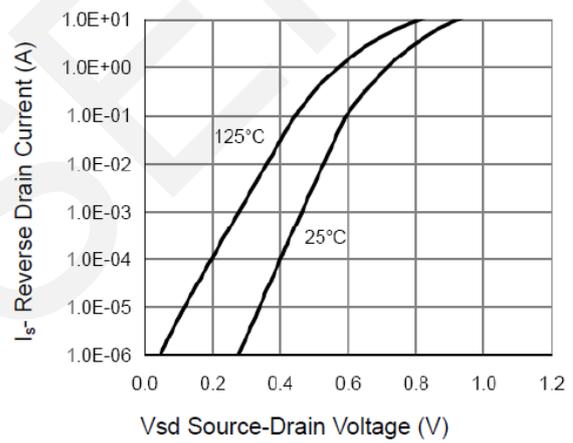
Rdson vs Vgs



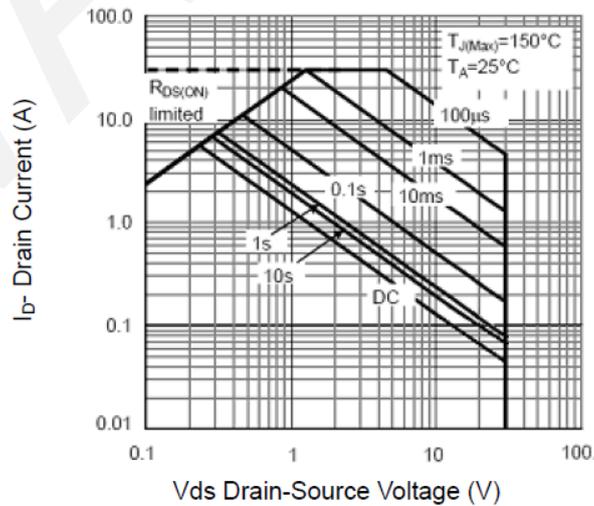
Capacitance vs Vds



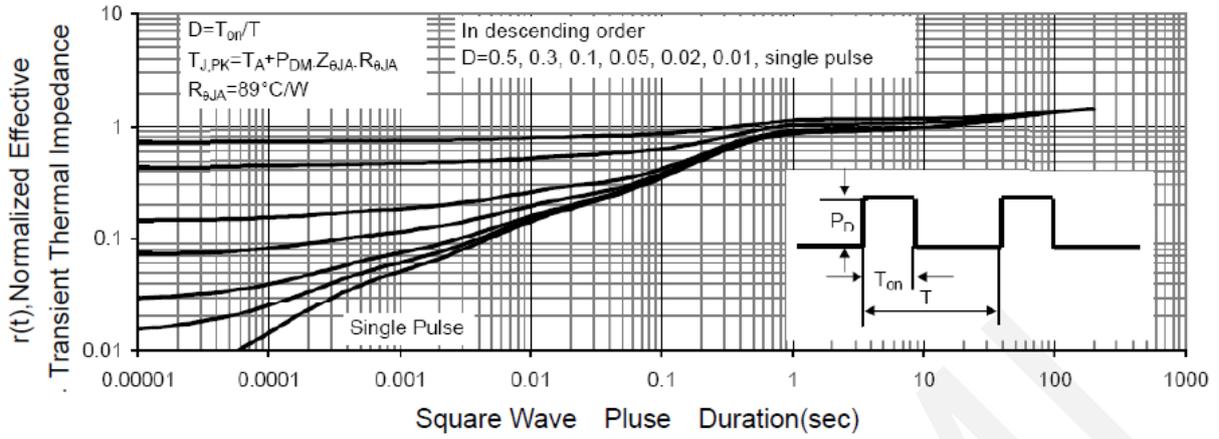
Gate Charge



Source- Drain Diode Forward



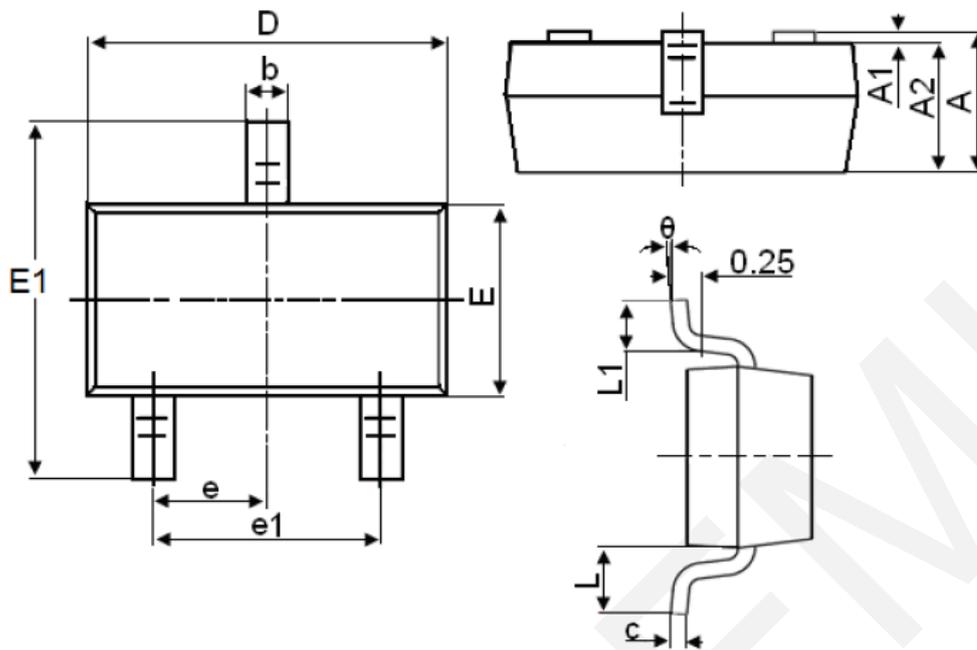
Safe Operation Area



Normalized Maximum Transient Thermal Impedance



**8.Package Dimensions**



Symbol	Dimensions in Millimeters		
	MIN.	TYP.	MAX.
A	0.900		1.150
A1	0.000		0.100
A2	0.900		1.050
b	0.300		0.500
c	0.080		0.150
D	2.800		3.000
E	1.200		1.400
E1	2.250		2.550
e		0.950	
e1	1.800		2.000
L		0.550	
L1	0.300		0.500
θ	0°		8°

## 9. Important Notice

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